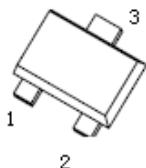


N-Channel MOSFET

V_{(BR)DSS}	R_{DS(on)MAX}	I_D
30V	8Ω@4V	100mA
	13Ω@2.5V	

SOT-723



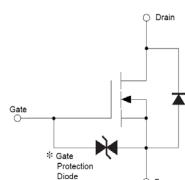
FEATURE

- Low on-resistance
- Fast switching speed
- Low voltage drive makes this device ideal for Portable equipment
- Drive circuits can be simple
- Parallel use is easy

APPLICATION

- Interfacing , Switching

Equivalent Circuit



Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-source voltage	V _{DS}	30	V
Gate-source voltage	V _{GS}	±20	
Continuous drain current	I _D	±100	mA
Power dissipation	P _D	0.15	W
Thermal resistance from junction to ambient	R _{θJA}	833	°C/W
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	-55 ~+150	

* Pw≤10μs ,Duty cycle≤1%

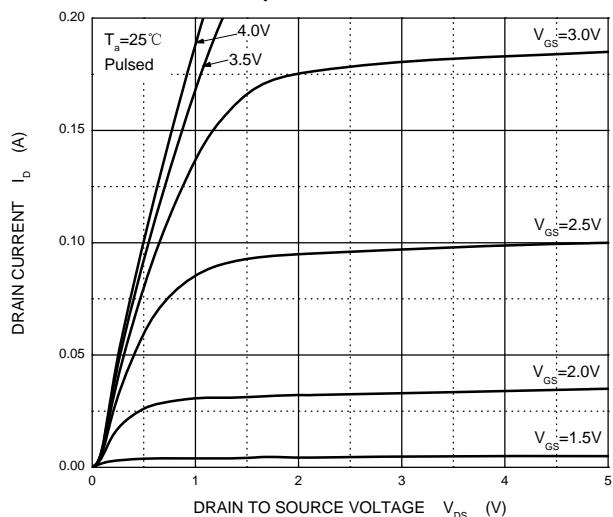
MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

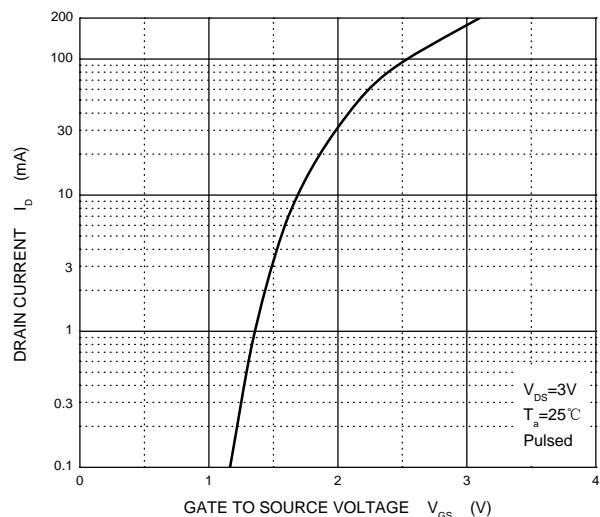
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 10\mu\text{A}$	30			V
Gate-source leakage current	I_{GSS}	$V_{\text{DS}} = 0\text{V}, V_{\text{GS}} = \pm 20\text{V}$			$\pm J$	μA
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 30\text{V}, V_{\text{GS}} = 0\text{V}$			1.0	μA
Gate threshold voltage	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = 3\text{V}, I_D = 100\mu\text{A}$	0.H		1.5	V
Static drain-source on-state resistance	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4\text{V}, I_D = 10\text{mA}$		5	8	Ω
		$V_{\text{GS}} = 2.5\text{V}, I_D = 1\text{mA}$		7	13	
Forward transconductance	g_{FS}	$V_{\text{DS}} = 3\text{V}, I_D = 10\text{mA}$	20			mS
Input capacitance	C_{iss}	$V_{\text{DS}} = 5\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		13		pF
Output capacitance	C_{oss}			9		
Reverse transfer capacitance	C_{rss}			4		
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{GS}} = 5\text{V}, V_{\text{DD}} = 5\text{V}, I_D = 10\text{mA}$ $R_L = 500\Omega, R_G = 10\Omega$		15		ns
Rise time	t_r			35		
Turn-off delay time	$t_{\text{d}(\text{off})}$			80		
Fall time	t_f			80		

Typical Characteristics

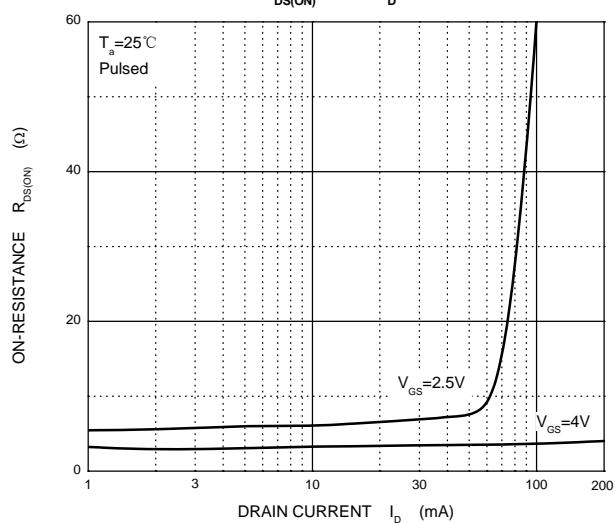
Output Characteristics



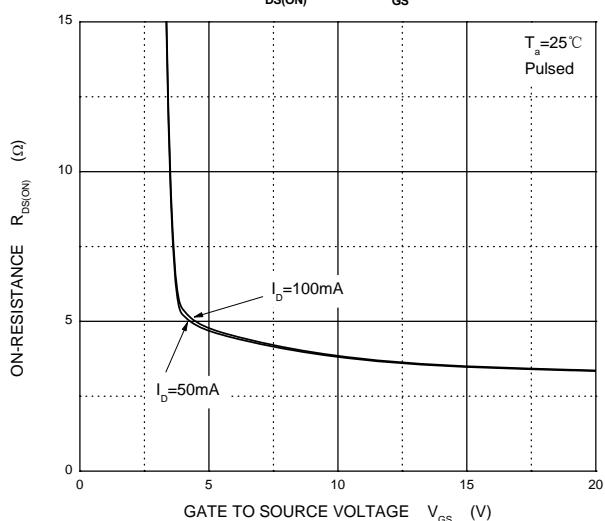
Transfer Characteristics



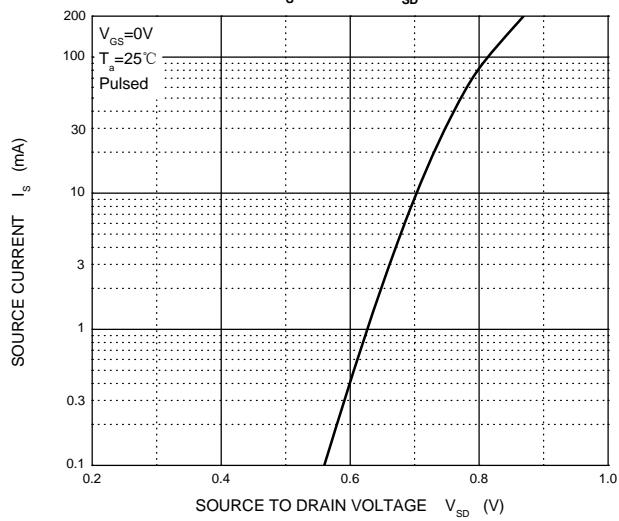
$R_{DS(ON)}$ — I_D



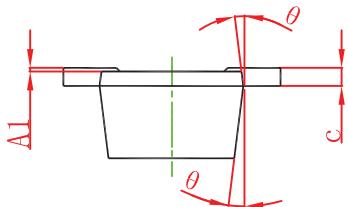
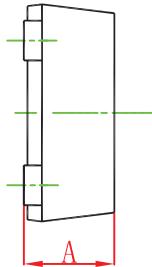
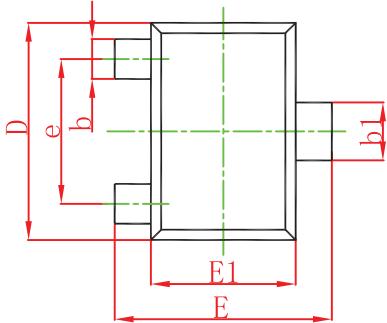
$R_{DS(ON)}$ — V_{GS}



I_s — V_{SD}

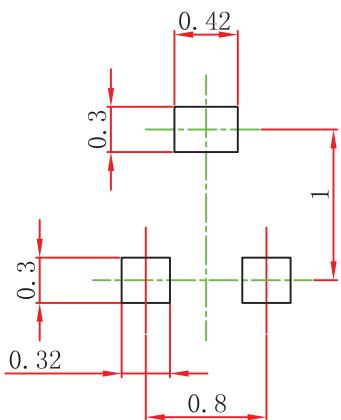


SOT-723 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.430	0.500	0.017	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

SOT-723 Suggested Pad Layout



Note:

1. Controlling dimension:in millimeters.
- 2.General tolerance: $\pm 0.05\text{mm}$.
- 3.The pad layout is for reference purposes only.